

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

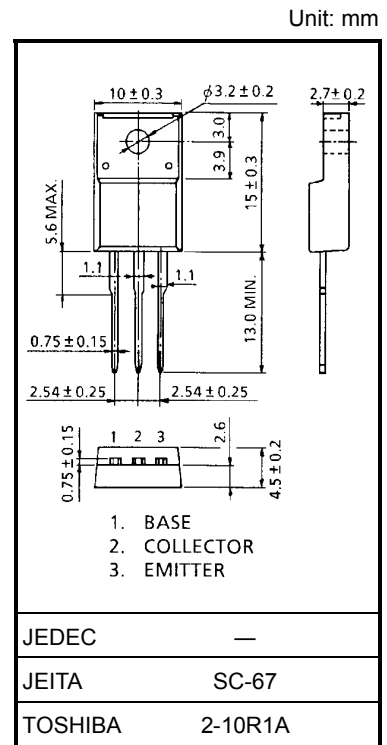
2SA1869

Power Amplifier Applications

- Good linearity of h_{FE}
- Complementary to 2SC4935

Maximum Ratings ($T_c = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-3	A
Base current	I_B	-0.3	A
Collector power dissipation ($T_c = 25^\circ\text{C}$)	P_C	10	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 150	$^\circ\text{C}$



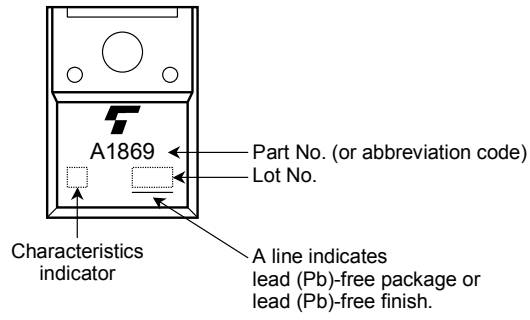
Electrical Characteristics ($T_c = 25^\circ\text{C}$)

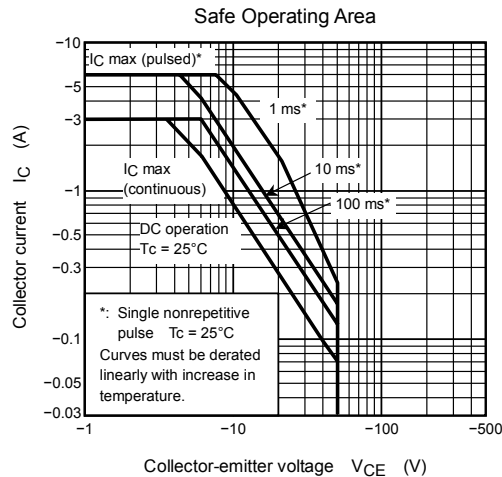
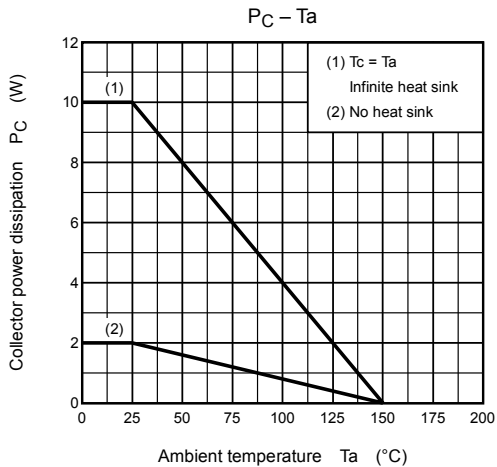
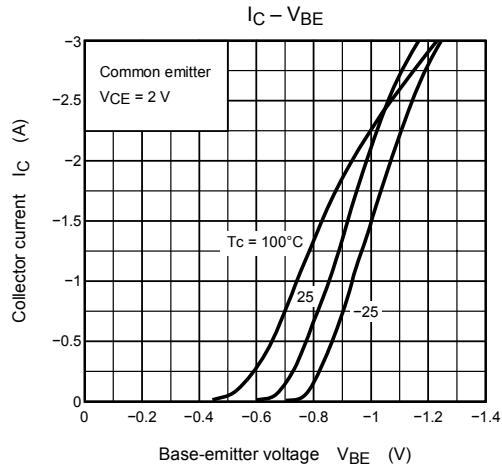
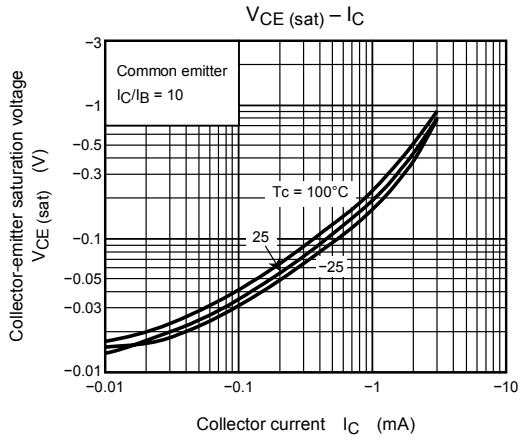
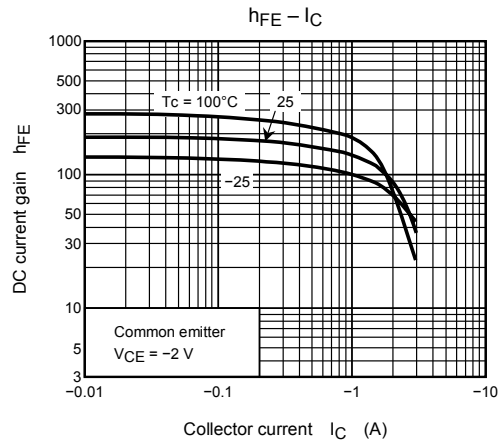
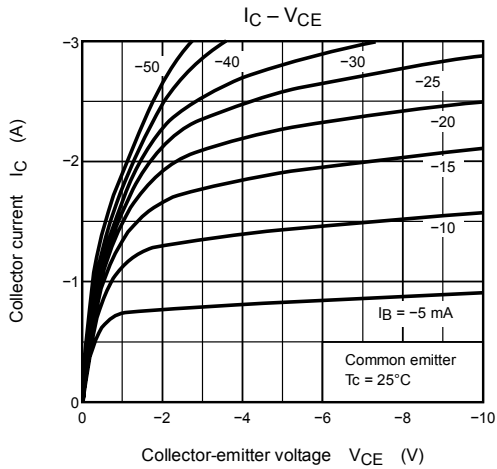
Weight: 1.7 g (typ.)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -50\text{ V}, I_E = 0$	—	—	-1.0	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-1.0	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{ mA}, I_B = 0$	-50	—	—	V
DC current gain	$h_{FE(1)}$ (Note)	$V_{CE} = -2\text{ V}, I_C = -0.5\text{ A}$	70	—	240	
	$h_{FE(2)}$	$V_{CE} = -2\text{ V}, I_C = -2.5\text{ A}$	30	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{ A}, I_B = -0.2\text{ A}$	—	-0.3	-0.6	V
Base-emitter voltage	V_{BE}	$V_{CE} = -2\text{ V}, I_C = -0.5\text{ A}$	—	-0.8	-1.0	V
Transition frequency	f_T	$V_{CE} = -2\text{ V}, I_C = -0.5\text{ A}$	—	100	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	35	—	pF

Note: $h_{FE(1)}$ classification O: 70 to 140, Y: 120 to 240

Marking





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